

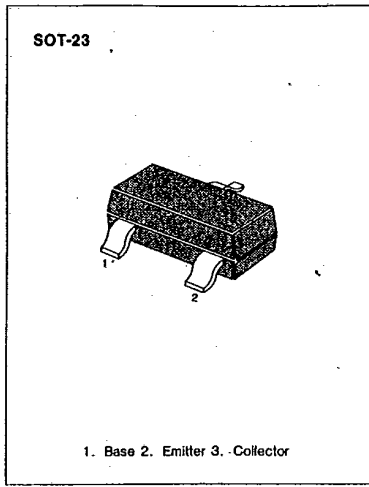
**KSR2105**

**PNP EPITAXIAL SILICON TRANSISTOR**

T-37-13

**SWITCHING APPLICATION (Bias Resistor Built In)**

- Switching Circuit, Inverter, Interface circuit  
Driver circuit
- Built in bias Resistor ( $R_1=4.7K\Omega$ ,  $R_2=10K\Omega$ )
- Complement to KSR1105



**ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )**

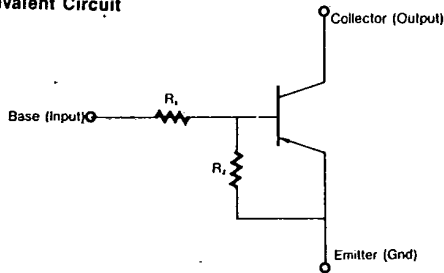
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-10	V
Collector Current	$I_C$	-100	mA
Collector Dissipation	$P_C$	200	mW
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55~150	$^\circ C$

3

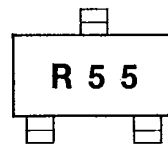
**ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C=-10\mu A, I_E=0$	-50			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C=-100\mu A, I_B=0$	-50			V
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=-40V, I_E=0$			-0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=-5V, I_C=-5mA$	30			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-10mA, I_B=-0.5mA$			-0.3	V
Current Gain-Bandwidth Product	Cob	$V_{CB}=-10V, I_E=0$ $f=1MHz$		5.5		pF
Current Gain-Bandwidth Product	$f_T$	$V_{CE}=-10V, I_C=-5mA$		200		MHz
Input Off Voltage	$V_i(off)$	$V_{CE}=-5V, I_C=-100\mu A$	-0.3			V
Input On Voltage	$V_i(on)$	$V_{CE}=-0.3V, I_C=-20mA$			-2.5	V
Input Resistor	$R_1$		3.2	4.7	6.2	$K\Omega$
Resistor Ratio	$R_1/R_2$		0.42	0.47	0.52	

**Equivalent Circuit**



**Marking**



**KSR2105**

**PNP EPITAXIAL SILICON TRANSISTOR**

T-37-13

